# Lonten N-channel 650V, 10A Power MOSFET

## Description

The Power MOSFET is fabricated using the advanced planer VDMOS technology. The resulting device has low conduction resistance, superior switching performance and high avalanche energy.

## Features

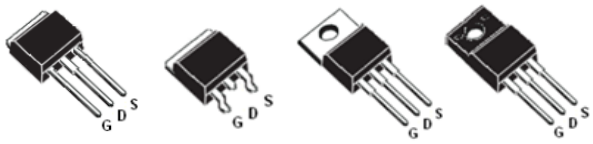
- Low $R_{DS(on)}$
- Low gate charge (typ. $Q_g$ = 34.2 nC)
- 100% UIS tested
- RoHS compliant

## Applications

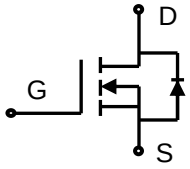
- Power factor correction.
- Switched mode power supplies.
- LED driver.

## Product Summary

| | |
|---|---|
| $V_{DSS}$ | 650V |
| $I_D$ | 10A |
| $R_{DS(on),max}$ | 1.0Ω |
| $Q_{g,typ}$ | 34.2 nC |




**TO-262** **TO-263** **TO-220** **TO-220F**




N-Channel MOSFET

## Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DSS}$ | 650 | V |
| Continuous drain current ( $T_C$ = 25°C ) | $I_D$ | 10 | A |
| ( $T_C$ = 100°C ) | | 6.3 | A |
| Pulsed drain current [1] | $I_{DM}$ | 40 | A |
| Gate-Source voltage | $V_{GSS}$ | ±30 | V |
| Avalanche energy, single pulse [2] | $E_{AS}$ | 500 | mJ |
| Peak diode recovery dv/dt [3] | dv/dt | 5 | V/ns |
| Power Dissipation TO-220F ( $T_C$ = 25°C ) | $P_D$ | 40 | W |
| Derate above 25°C | | 0.32 | W/°C |
| Power Dissipation TO-220\ TO-262\ TO-263 ( $T_C$ = 25°C ) | | 130 | W |
| Derate above 25°C | | 1.04 | W/°C |
| Operating junction and storage temperature range | $T_J$, $T_{STG}$ | -55 to +150 | °C |
| Continuous diode forward current | $I_S$ | 10 | A |
| Diode pulse current | $I_{S,pulse}$ | 40 | A |

## Thermal Characteristics

| Parameter | Symbol | Value | | Unit |
|---|---|---|---|---|
| | | TO-220F | TO-220\TO-251\TO-252 | |
| Thermal resistance, Junction-to-case | $R_{\theta JC}$ | 3.13 | 0.96 | °C/W |
| Thermal resistance, Junction-to-ambient | $R_{\theta JA}$ | 110 | 62.5 | °C/W |

## Package Marking and Ordering Information

| Device | Device Package | Marking | Units/Tube | Units/Real |
|---|---|---|---|---|
| LNC10N65 | TO-220 | LNC10N65 | 50 | |
| LND10N65 | TO-220F | LND10N65 | 50 | |
| LNE10N65 | TO-263 | LNE10N65 | 50 | |
| LNF10N65 | TO-262 | LNF10N65 | 50 | |

## Electrical Characteristics

$T_c$ = 25°C unless otherwise noted

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | |
| Drain-source breakdown voltage | $BV_{DSS}$ | $V_{GS}$=0 V, $I_D$=0.25 mA | 650 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}$=$V_{GS}$, $I_D$=0.25 mA | 2 | - | 4 | V |
| Drain cut-off current | $I_{DSS}$ | $V_{DS}$=650 V, $V_{GS}$=0 V,<br>$T_j$ = 25°C<br>$T_j$ = 125°C | <br>-<br>- | <br>- | <br>1<br>100 | <br>μA |
| Gate leakage current, Forward | $I_{GSSF}$ | $V_{GS}$=30 V, $V_{DS}$=0 V | - | - | 100 | nA |
| Gate leakage current, Reverse | $I_{GSSR}$ | $V_{GS}$=-30 V, $V_{DS}$=0 V | - | - | -100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}$=10 V, $I_D$=5A | - | 0.81 | 1.0 | Ω |
| **Dynamic characteristics** | | | | | | |
| Input capacitance | $C_{iss}$ | $V_{DS}$ = 25 V, $V_{GS}$ = 0 V, | - | 1622 | - | |
| Output capacitance | $C_{oss}$ | f = 1 MHz | - | 144.2 | - | pF |
| Reverse transfer capacitance | $C_{rss}$ | | - | 6.8 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}$ = 325 V, $I_D$ = 10 A | - | 14.16 | - | |
| Rise time | $t_r$ | $R_G$ = 10 Ω, $V_{GS}$=15 V | - | 34.64 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 65.72 | - | |
| Fall time | $t_f$ | | - | 16.04 | - | |
| **Gate charge characteristics** | | | | | | |
| Gate to source charge | $Q_{gs}$ | $V_{DD}$=520 V, $I_D$=10 A, | - | 8.8 | - | |
| Gate to drain charge | $Q_{gd}$ | $V_{GS}$=0 to 10 V | - | 12.89 | - | nC |
| Gate charge total | $Q_g$ | | - | 34.2 | - | |
| Gate plateau voltage | $V_{plateau}$ | | - | 5 | - | V |
| **Reverse diode characteristics** | | | | | | |
| Diode forward voltage | $V_{SD}$ | $V_{GS}$=0 V, $I_F$=10 A | - | - | 1.5 | V |
| Reverse recovery time | $t_{rr}$ | $V_R$=325 V, $I_F$=10 A, | - | 418.8 | - | ns |
| Reverse recovery charge | $Q_{rr}$ | $dI_F/dt$=100 A/μs | - | 3.40 | - | μC |
| Peak reverse recovery current | $I_{rrm}$ | | - | 16.28 | - | A |

Notes:

1. Pulse width limited by maximum junction temperature.

2. L=10mH, $I_{AS}$ = 10A, Starting $T_j$= 25°C.

3. $I_{SD}$ = 10A, di/dt≤100A/us, $V_{DD}$≤$BV_{DS}$, Starting $T_j$= 25°C.

## Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

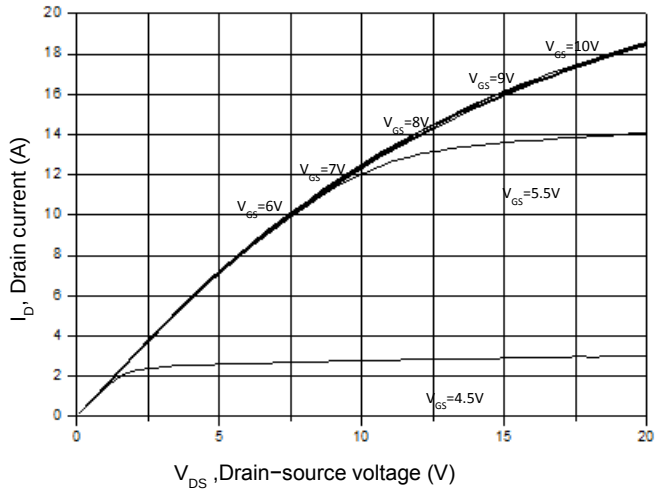



Figure 2. Transfer Characteristics

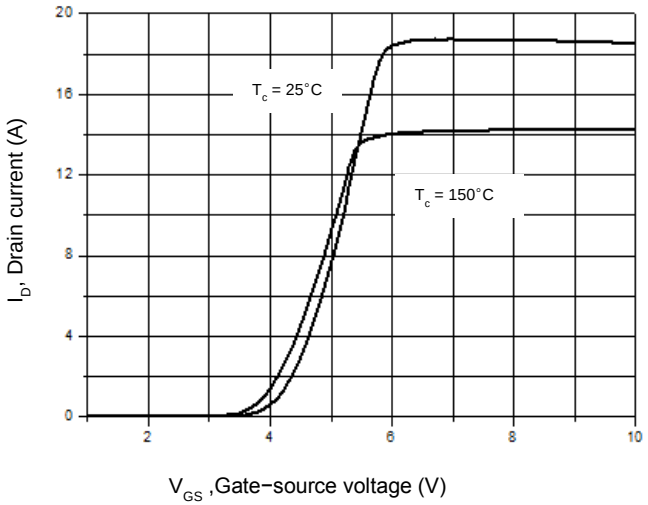



Figure 3. On-Resistance Variation vs. Drain Current

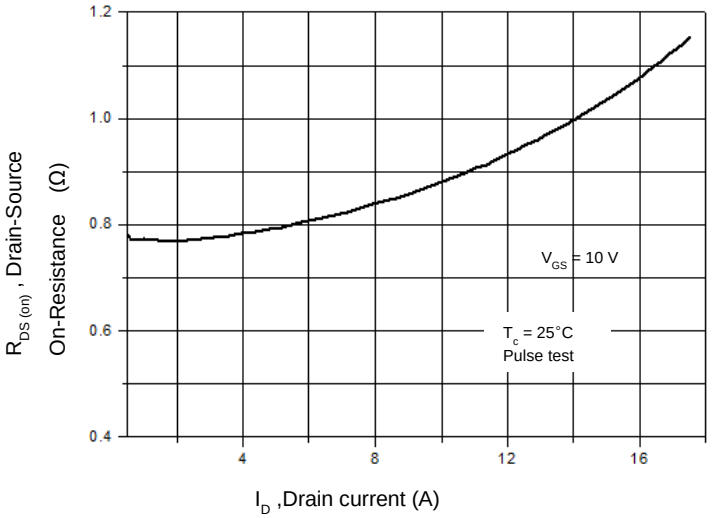



Figure 4. Threshold Voltage vs. Temperature

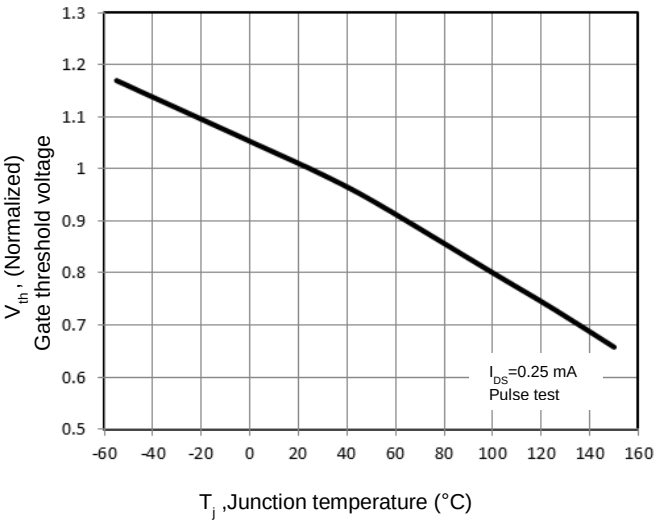



Figure 5. Breakdown Voltage vs. Temperature

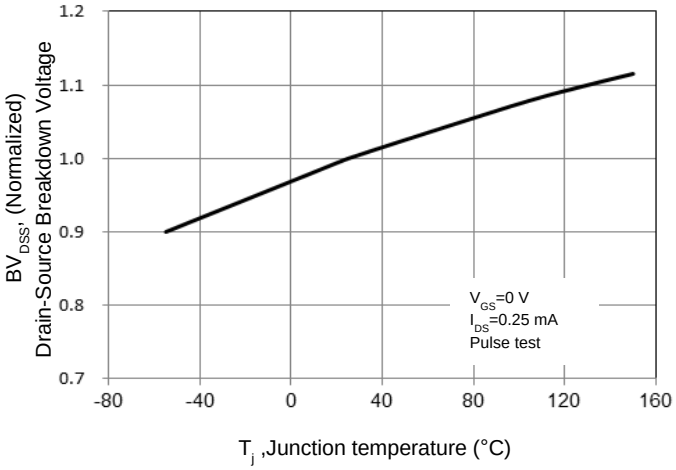



Figure 6. On-Resistance vs. Temperature

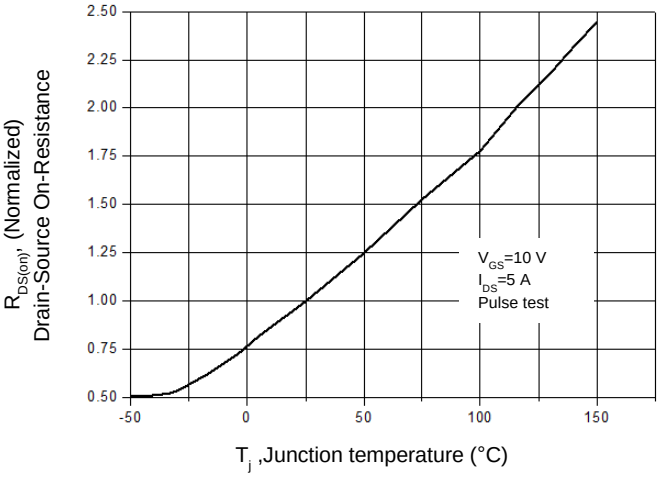


Figure 7. Capacitance Characteristics

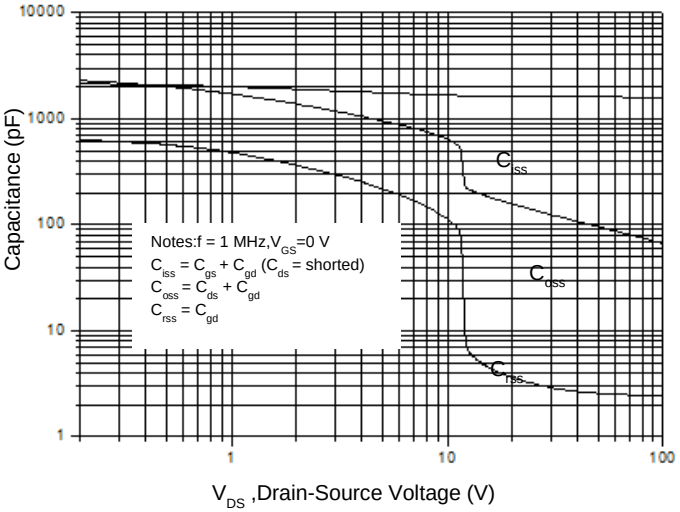



Figure 8. Gate Charge Characteristics

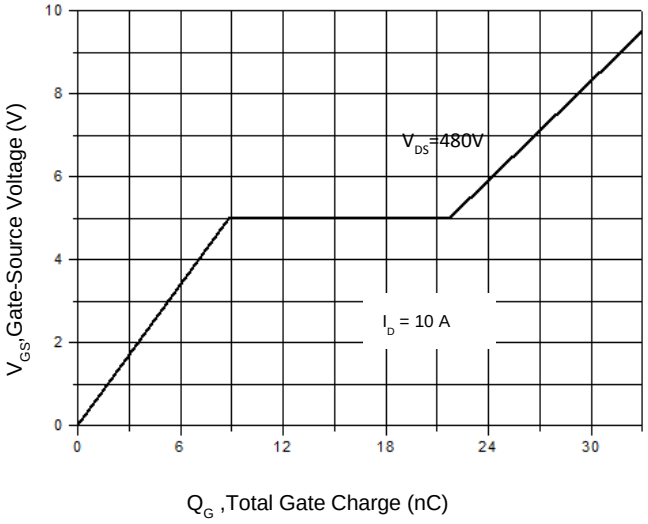



Figure 9. Maximum Safe Operating Area

TO-220F

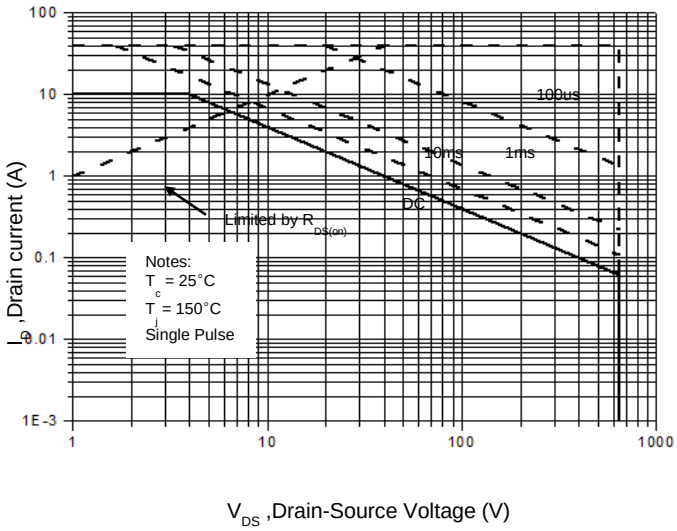



Figure 10. Maximum Safe Operating Area

TO-220/ TO-262/TO-263

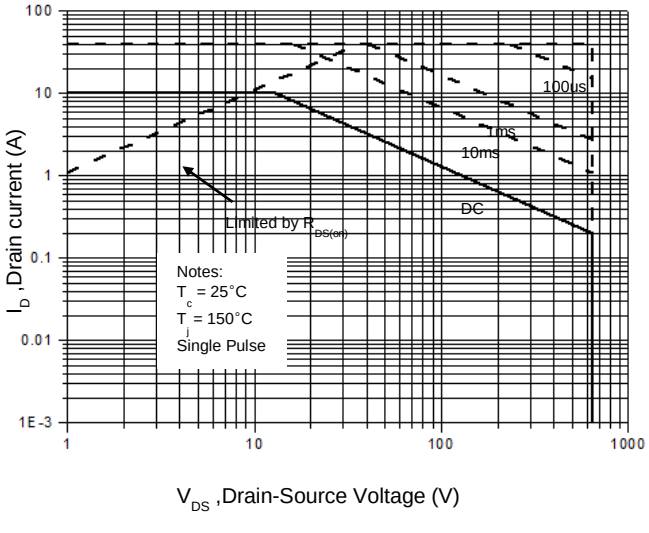



Figure 11. Power Dissipation vs. Temperature

TO-220F

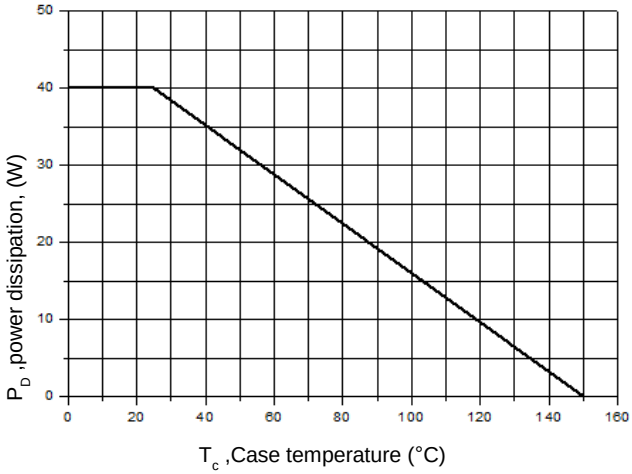



Figure 12. Power Dissipation vs. Temperature

TO-220/ TO-262/TO-263

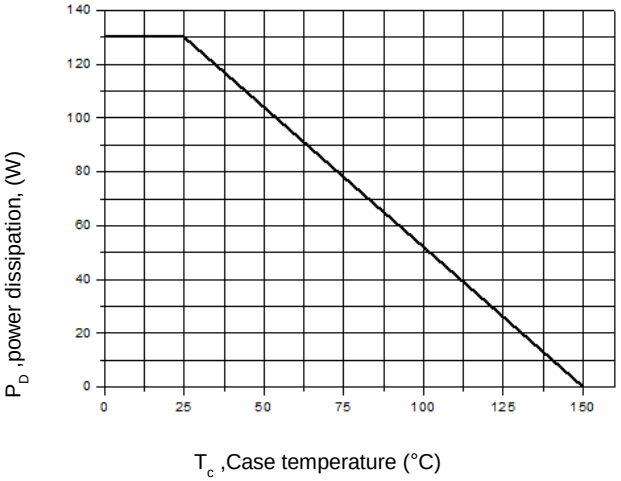


Figure 13. Continuous Drain Current vs. Temperature

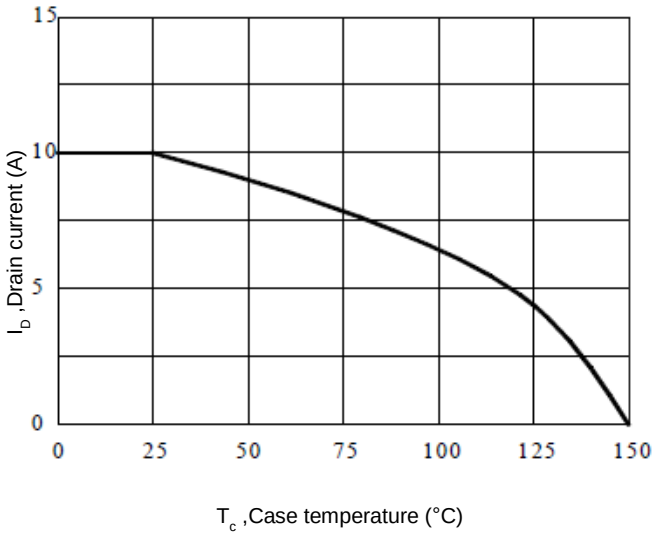



Figure 14. Body Diode Transfer Characteristics

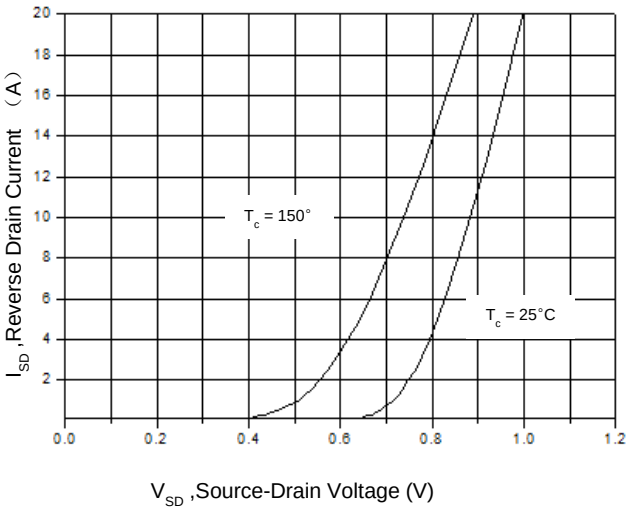



Figure 15 Transient Thermal Impedance, Junction to Case, TO-220F

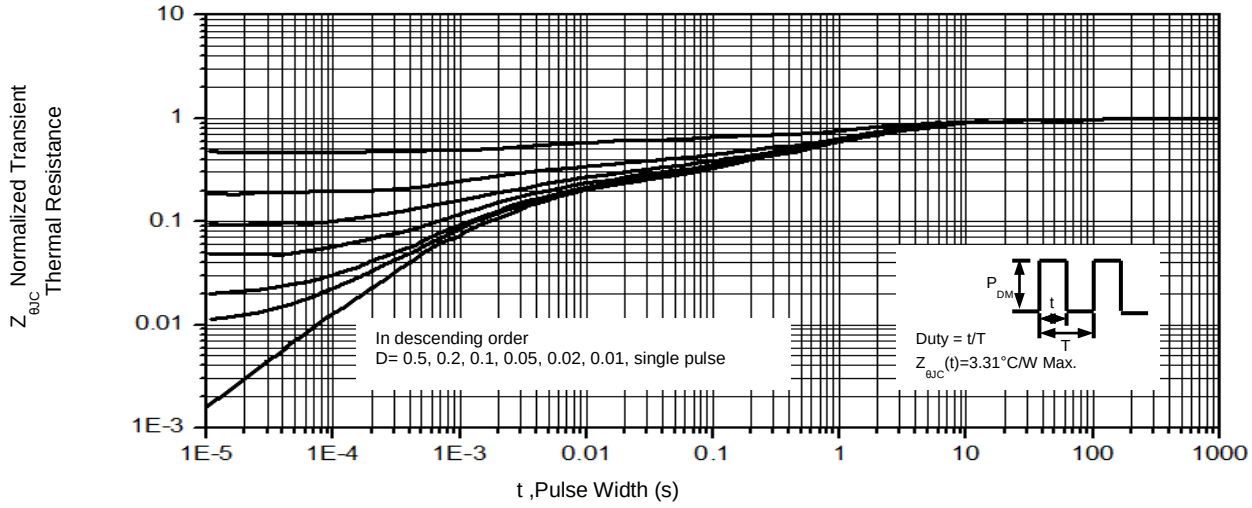
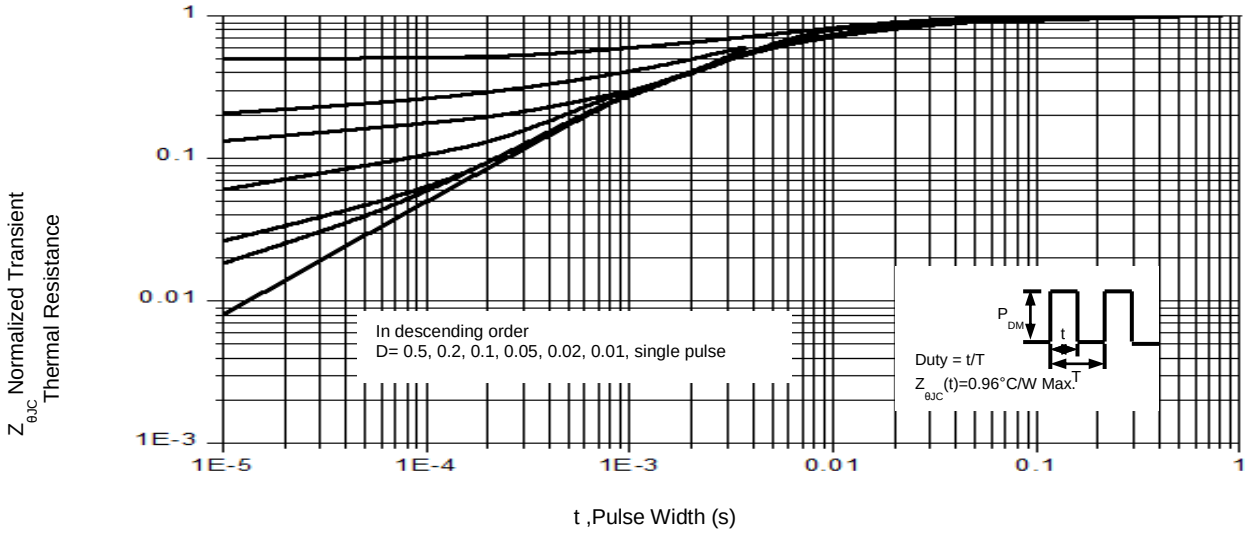
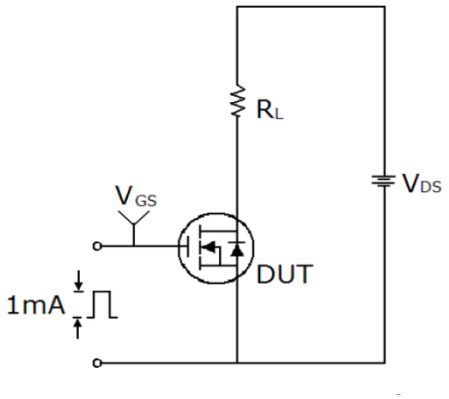
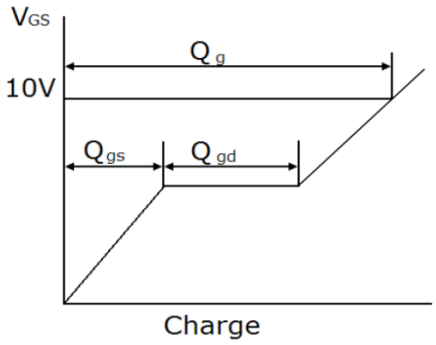


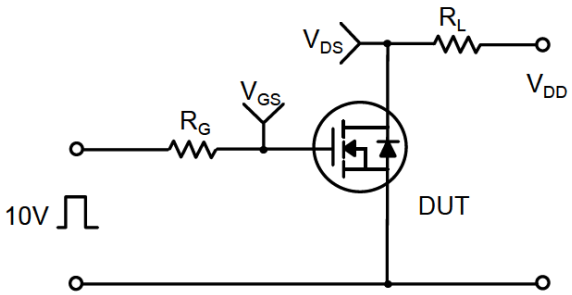

Figure 16. Transient Thermal Impedance, Junction to Case, TO-220/ TO-262/TO-263

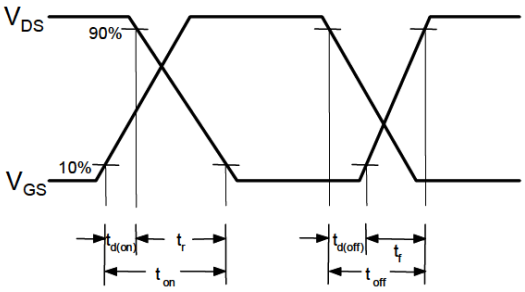


## Gate Charge Test Circuit & Waveform

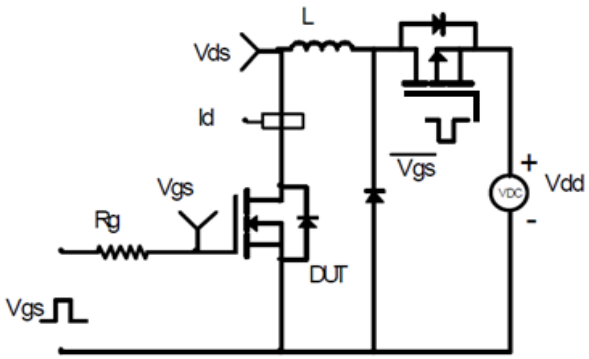


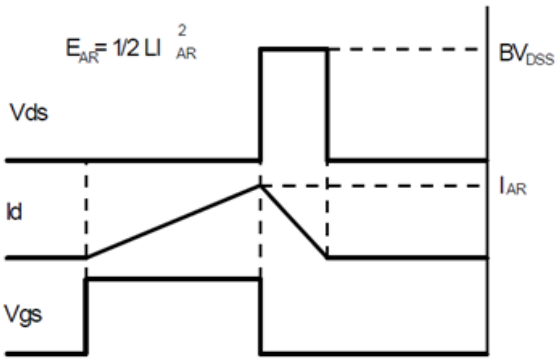



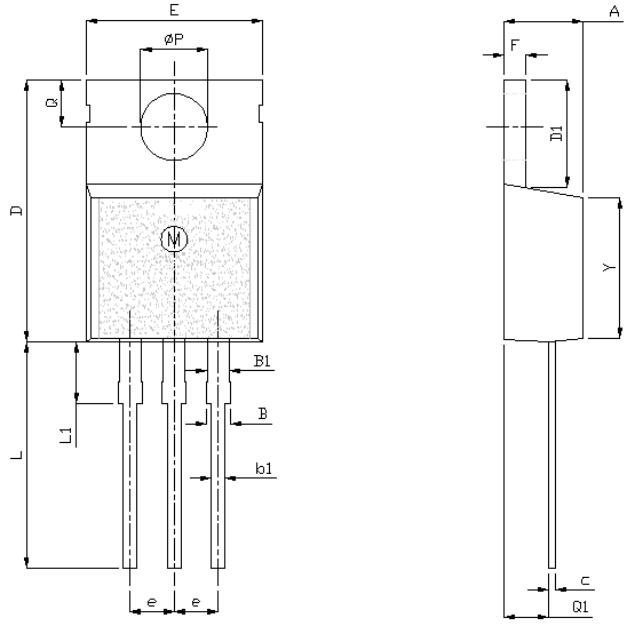




## Unclamped Inductive Switching Test Circuit & Waveforms



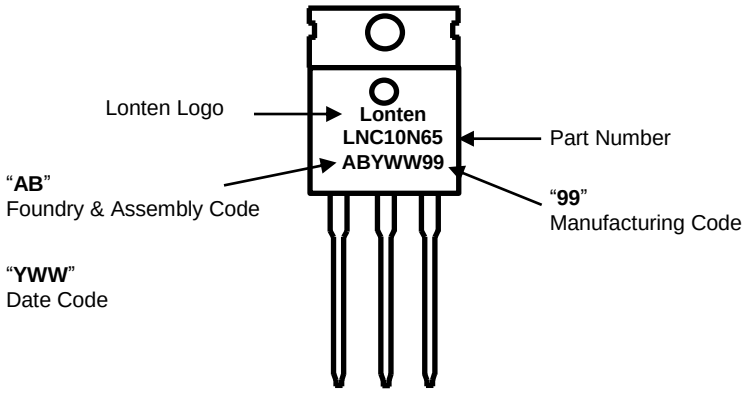
## Mechanical Dimensions for TO-220



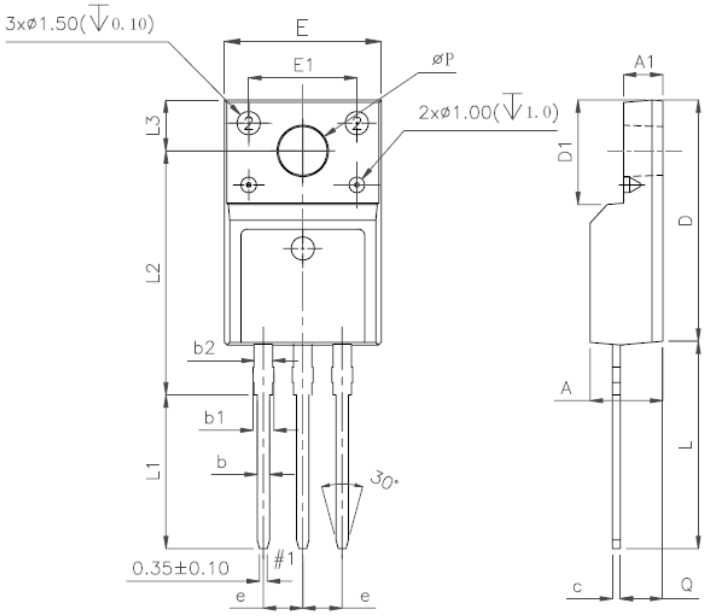

UNIT：mm

| SYMBOL | MIN | NOM | MAX |
|---|---|---|---|
| A | 4 | | 4.8 |
| B | 1.2 | | 1.4 |
| B1 | 1 | | 1.4 |
| b1 | 0.75 | | 0.95 |
| c | 0.4 | | 0.55 |
| D | 15 | | 16.5 |
| D1 | 5.9 | | 6.9 |
| E | 9.9 | | 10.7 |
| e | 2.44 | 2.54 | 2.64 |
| F | 1.1 | | 1.4 |
| L | 12.5 | | 14.5 |
| L1 | 3 | 3.5 | 4 |
| ΦP | 3.7 | 3.8 | 3.9 |
| Q | 2.5 | | 3 |
| Q1 | 2 | | 2.9 |
| Y | 8.02 | 8.12 | 8.22 |

## TO-220 Part Marking Information



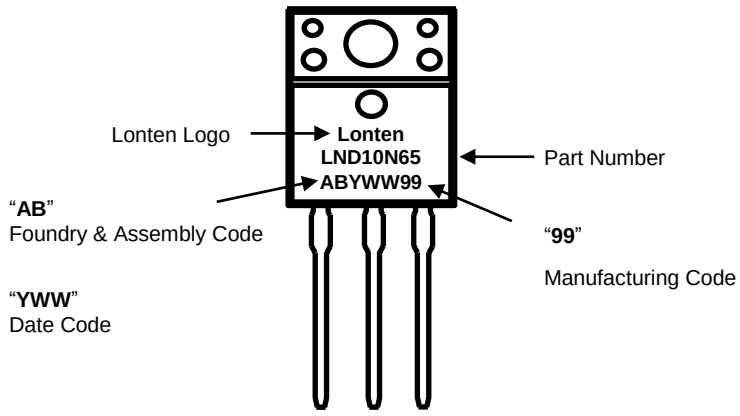
## Mechanical Dimensions for TO-220F



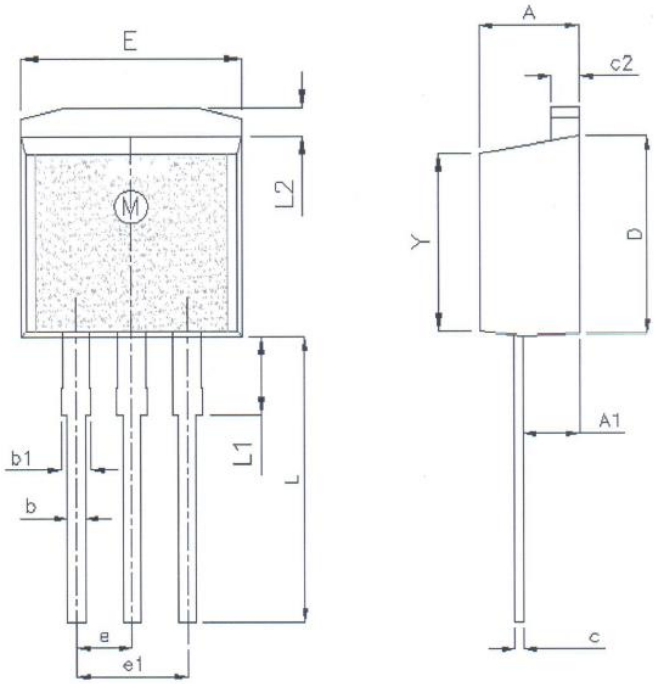

UNIT：mm

| SYMBOL | MIN | NOM | MAX |
|---|---|---|---|
| A | 4.5 | | 4.9 |
| A1 | 2.3 | | 2.9 |
| b | 0.65 | | 0.9 |
| b1 | 1.1 | | 1.7 |
| b2 | 1.2 | | 1.4 |
| c | 0.35 | | 0.65 |
| D | 14.5 | | 16.5 |
| D1 | 6.1 | | 6.9 |
| E | 9.6 | | 10.3 |
| E1 | 6.5 | 7 | 7.5 |
| e | 2.44 | 2.54 | 2.64 |
| L | 12.5 | | 14.3 |
| L1 | 9.45 | | 10.05 |
| L2 | 15 | | 16 |
| L3 | 3.2 | | 4.4 |
| ΦP | 3 | | 3.3 |
| Q | 2.5 | | 2.9 |

## TO-220F Part Marking Information



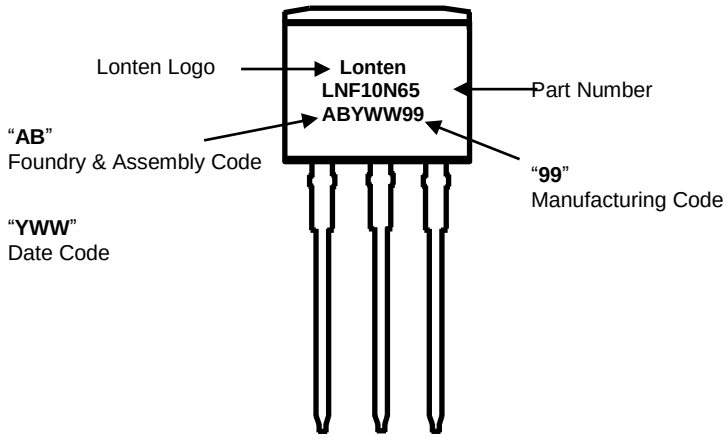
## Mechanical Dimensions for TO-262



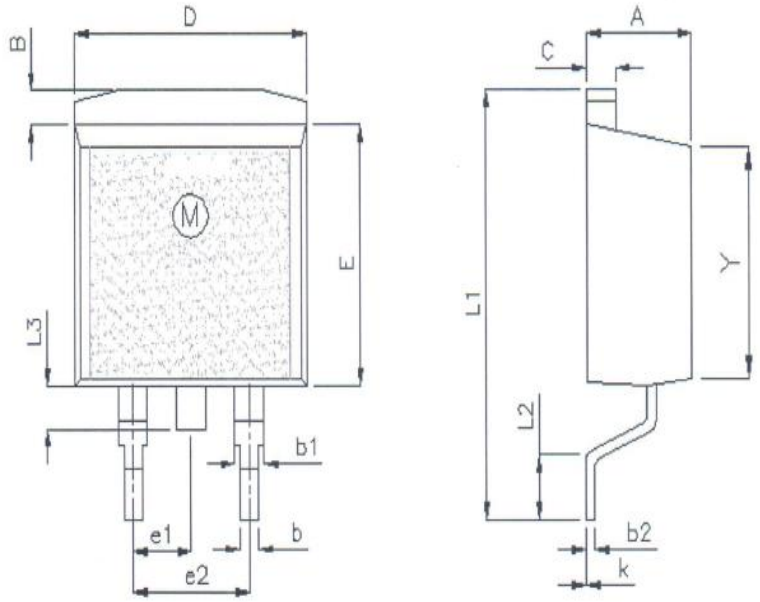

UNIT：mm

| SYMBOL | MIN | NOM | MAX |
|---|---|---|---|
| A | 4.42 | | 4.72 |
| A1 | 2.40 | | 2.80 |
| b | 0.76 | | 0.86 |
| b1 | 1.22 | | 1.40 |
| c | 0.33 | | 0.43 |
| c2 | 1.22 | | 1.35 |
| D | 8.99 | | 9.29 |
| e | 2.44 | 2.54 | 2.64 |
| e1 | 4.98 | | 5.18 |
| E | 9.95 | | 10.25 |
| L | 12.50 | | 13.60 |
| L1 | 3.30 | 3.50 | 3.80 |
| L2 | 1.22 | | 1.40 |
| Y | 8.02 | 8.12 | 8.22 |

## TO-262 Part Marking Information



## Mechanical Dimensions for TO-263




UNIT：mm

| SYMBOL | MIN | NOM | MAX |
|---|---|---|---|
| A | 4.42 | | 4.72 |
| B | 1.22 | | 1.4 |
| b | 0.76 | | 0.86 |
| b1 | 1.22 | | 1.4 |
| b2 | 0.33 | | 0.43 |
| C | 1.22 | | 1.35 |
| D | 9.95 | | 10.25 |
| E | 8.99 | | 9.29 |
| e1 | 2.44 | 2.54 | 2.64 |
| e2 | 4.98 | | 5.18 |
| L1 | 14.7 | 15.1 | 15.5 |
| L2 | 2 | 2.3 | 2.6 |
| L3 | 1.5 | | 2 |
| K | -0.1 | | 0.1 |
| Y | 8.02 | 8.12 | 8.22 |

## TO-263 Part Marking Information